

AN 1987-196552 [28] WPIDS
DNN N1987-147048 DNC C1987-082359
TI Bonding wire for semiconductor device e.g. IC, LSI - comprises copper
contg. sulphur matrix, and indium, magnesium, beryllium, **boron**,
zirconium, silver, silicon, calcium etc..
DC L03 M26 U11 X12
PA (NIHA) NIPPON MINING CO; (TATD) TATSUTA DENSEN KK
CYC 1
PI JP 62127438 A 19870609 (198728)* 5p
JP 03079416 B 19911218 (199203)
ADT JP 62127438 A JP 1985-265621 19851126; JP 03079416 B JP 1985-265621
19851126
PRAI JP 1985-265621 19851126
AB JP 62127438 A UPAB: 19930922
The bonding wire comprises Cu having 99.999
wt.% or over purity, contg. 0.0005 wt.% or less S, as a matrix, to which
as additive elements, less than 0.02 wt.% (A) In and Mg, as a total, and
0.01 wt.% or less (B) at least one of Be, B, Zr, Y,
Ag, Si, Ca, and rare earth elements, but 0.02 wt.% or less (A)+(B
) groups, are added.
USE - The bonding wire is used for connection between electrodes on
semiconductor devices such as transistors, IC's, and LSI's, and outer
leads. With the wire, heat resistance, fracture strength and bonding
characteristics can be improved.
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